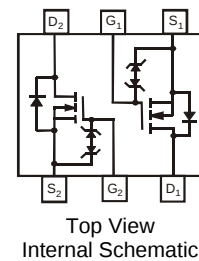


## Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **ESD Protected up to 2KV**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 standards for High Reliability**

## Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



## Ordering Information (Note 3)

| Part Number  | Case   | Packaging        |
|--------------|--------|------------------|
| DMN2004DWK-7 | SOT363 | 3000/Tape & Reel |

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



NAB = Marking Code  
YM = Date Code Marking  
Y = Year (ex: T = 2006)  
M = Month (ex: 9 = September)

### Date Code Key

| Year  | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code  | T    | U    | V    | W    | X    | Y    | Z    | A    | B    | C    | D    | E    |
| Month | Jan  | Feb  | Mar  | Apr  | May  | Jun  | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
| Code  | 1    | 2    | 3    | 4    | 5    | 6    | 7    | 8    | 9    | O    | N    | D    |

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                |              |                       | Symbol           | Value | Units |
|-------------------------------|--------------|-----------------------|------------------|-------|-------|
| Drain-Source Voltage          |              |                       | V <sub>DSS</sub> | 20    | V     |
| Gate-Source Voltage           |              |                       | V <sub>GSS</sub> | ±8    | V     |
| Drain Current (Note 4)        | Steady State | T <sub>A</sub> = 25°C | I <sub>D</sub>   | 540   | mA    |
|                               |              | T <sub>A</sub> = 85°C |                  | 390   |       |
| Pulsed Drain Current (Note 5) |              |                       | I <sub>DM</sub>  | 1.5   | A     |

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                          | Symbol                            | Value       | Units |
|-----------------------------------------|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 4)        | P <sub>D</sub>                    | 200         | mW    |
| Thermal Resistance, Junction to Ambient | R <sub>θJA</sub>                  | 625         | °C/W  |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -65 to +150 | °C    |

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                      | Symbol              | Min | Typ | Max  | Unit | Test Condition                                             |
|-------------------------------------|---------------------|-----|-----|------|------|------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 6)</b> |                     |     |     |      |      |                                                            |
| Drain-Source Breakdown Voltage      | BV <sub>DSS</sub>   | 20  | —   | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA                |
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>    | —   | —   | 1    | μA   | V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V                |
| Gate-Source Leakage                 | I <sub>GSS</sub>    | —   | —   | ±1   | μA   | V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V              |
| <b>ON CHARACTERISTICS (Note 6)</b>  |                     |     |     |      |      |                                                            |
| Gate Threshold Voltage              | V <sub>GS(th)</sub> | 0.5 | —   | 1.0  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA |
| Static Drain-Source On-Resistance   | R <sub>DS(on)</sub> | —   | 0.4 | 0.55 | Ω    | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 540mA             |
|                                     |                     |     | 0.5 | 0.70 |      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 500mA             |
|                                     |                     |     | 0.7 | 0.9  |      | V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA             |
|                                     |                     |     | —   | —    |      | V <sub>GS</sub> = 1.6V, I <sub>D</sub> = 350mA             |
| Forward Transfer Admittance         | Y <sub>fs</sub>     | 200 | —   | —    | ms   | V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A               |
| Diode Forward Voltage (Note 6)      | V <sub>SD</sub>     | 0.5 | —   | 1.4  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA               |
| <b>DYNAMIC CHARACTERISTICS</b>      |                     |     |     |      |      |                                                            |
| Input Capacitance                   | C <sub>iss</sub>    | —   | —   | 150  | pF   | V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V<br>f = 1.0MHz  |
| Output Capacitance                  | C <sub>oss</sub>    | —   | —   | 25   | pF   |                                                            |
| Reverse Transfer Capacitance        | C <sub>rss</sub>    | —   | —   | 20   | pF   |                                                            |

- Notes: 4. Device mounted on FR-4 PCB.  
 5. Pulse width ≤10μs, Duty Cycle ≤1%.  
 6. Short duration pulse test used to minimize self-heating effect.

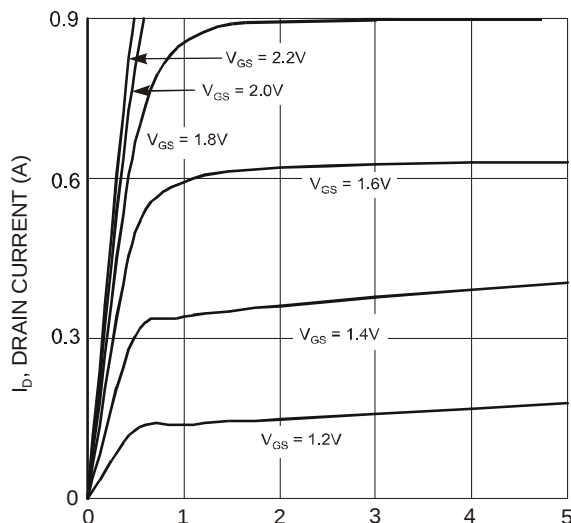


Fig. 1 Typical Output Characteristics

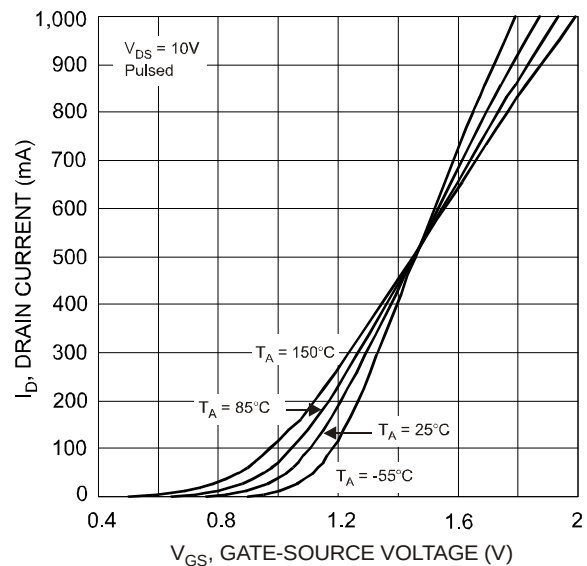


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

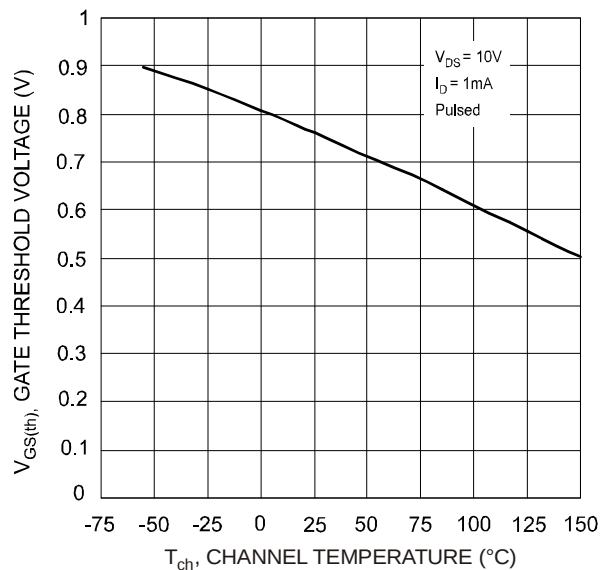


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

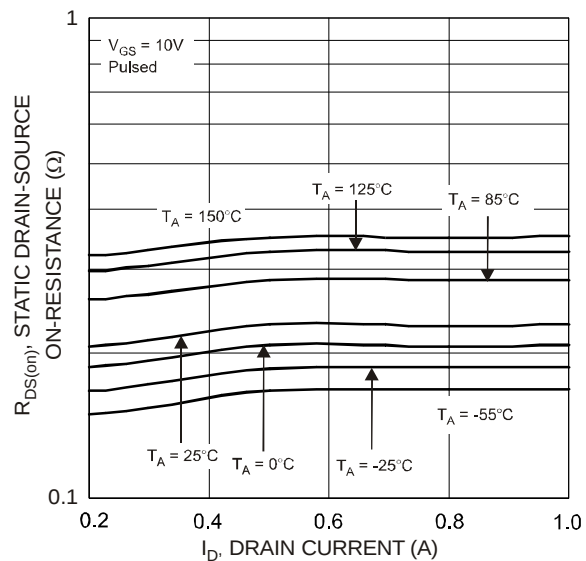


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

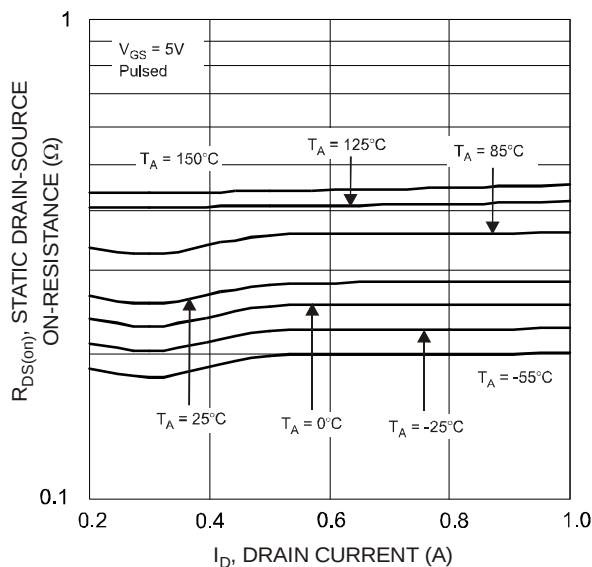


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

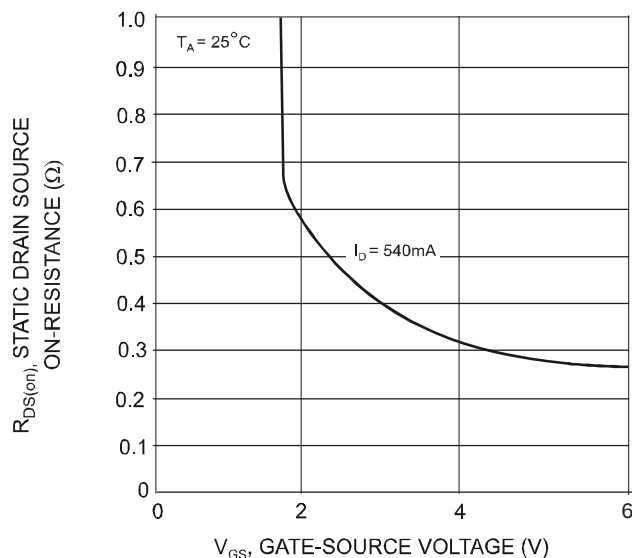


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

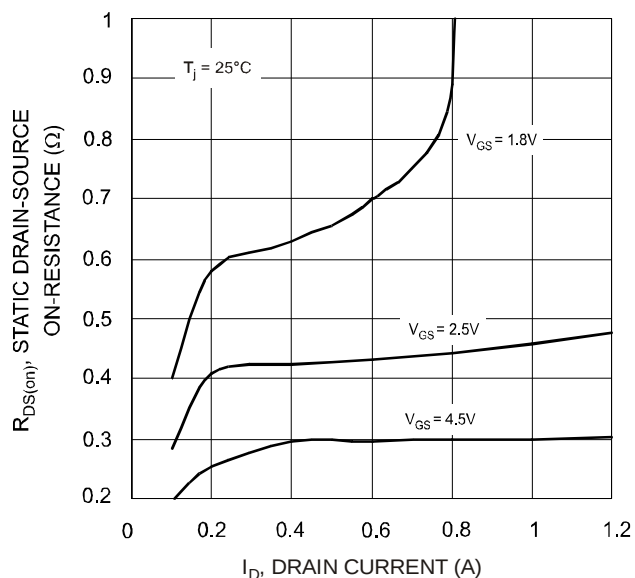


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

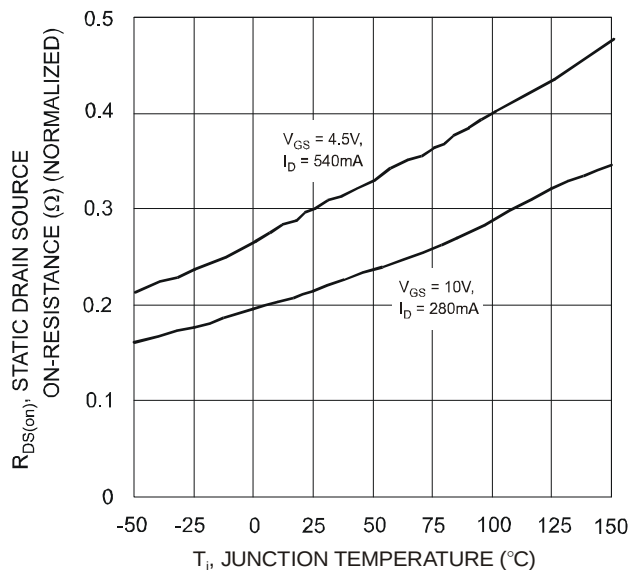


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

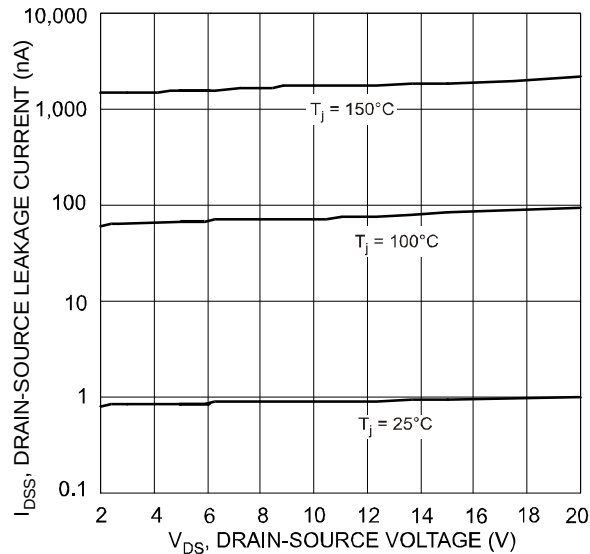


Fig. 9 Drain Source Leakage Current vs. Voltage

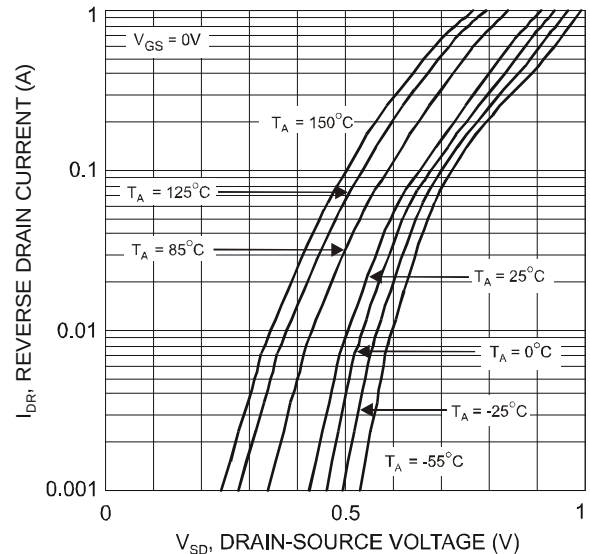


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

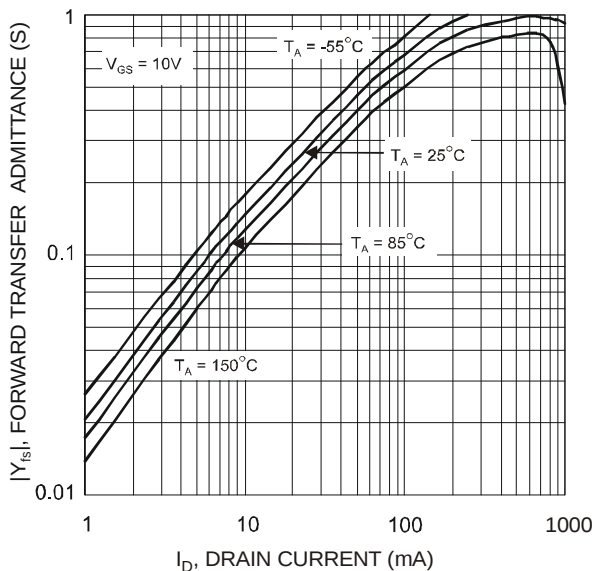


Fig. 11 Forward Transfer Admittance vs. Drain Current

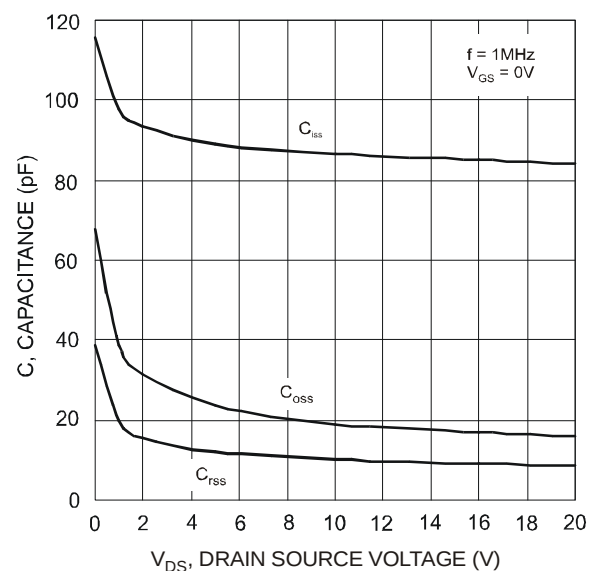
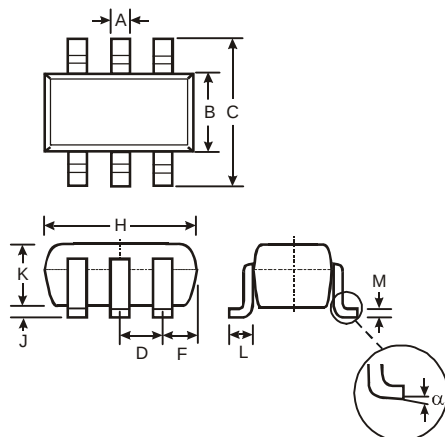


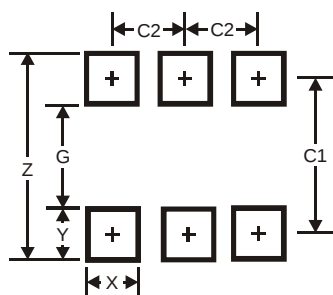
Fig. 12 Capacitance Variation

## Package Outline Dimensions



| SOT363               |          |      |
|----------------------|----------|------|
| Dim                  | Min      | Max  |
| A                    | 0.10     | 0.30 |
| B                    | 1.15     | 1.35 |
| C                    | 2.00     | 2.20 |
| D                    | 0.65 Typ |      |
| F                    | 0.40     | 0.45 |
| H                    | 1.80     | 2.20 |
| J                    | 0        | 0.10 |
| K                    | 0.90     | 1.00 |
| L                    | 0.25     | 0.40 |
| M                    | 0.10     | 0.22 |
| $\alpha$             | 0°       | 8°   |
| All Dimensions in mm |          |      |

## Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.5           |
| G          | 1.3           |
| X          | 0.42          |
| Y          | 0.6           |
| C1         | 1.9           |
| C2         | 0.65          |

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